

isc N-Channel MOSFET Transistor

1N50

• FEATURES

- Drain Current $I_D = 1.3A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 500V(\text{Min})$
- Static Drain-Source On-Resistance
: $R_{DS(on)} = 5.5 \Omega (\text{Max})$
- Fast Switching

• APPLICATIONS

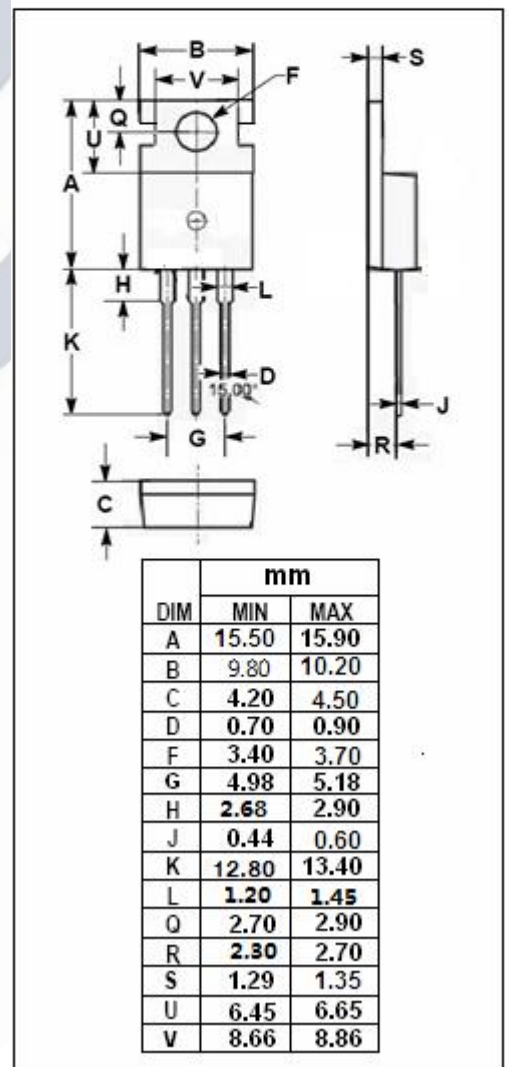
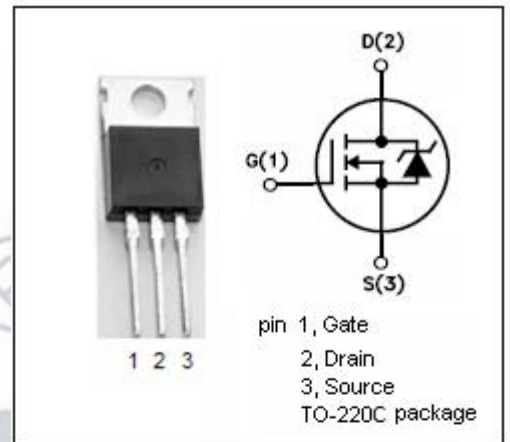
- Switch mode power supply.

• ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	500	V
V_{GS}	Gate-Source Voltage-Continuous	± 30	V
I_D	Drain Current-Continuous	1.3	A
I_{DM}	Drain Current-Single Plused	5	A
P_D	Total Dissipation @ $T_C = 25^\circ C$	40	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55~150	$^\circ C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R_{thj-c}	Thermal Resistance, Junction to Case	3.13	$^\circ C/W$



isc N-Channel MOSFET Transistor**1N50****• ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=250\mu\text{A}$	500			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=250\mu\text{A}$	2.0		4.0	V
V_{SD}	Diode Forward On-voltage	$I_S=1.3\text{A}; V_{GS}=0$			1.15	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}; I_D=0.65\text{A}$			5.5	Ω
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 30\text{V}; V_{DS}=0$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=500\text{V}; V_{GS}=0$			1	μA
t_r	Rise Time	$V_{GS}=10\text{V};$ $I_D=1.5\text{A};$ $V_{DD}=250\text{V};$ $R_L=24\Omega$		13	35	ns
$t_{d(on)}$	Turn-on Delay Time			12	35	
t_f	Fall Time			15	40	
$t_{d(off)}$	Turn-off Delay Time			42	90	